

PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of

Bernard DIENY et al.

Application No.: New U.S. National Stage of
PCT/FR2004/002517

Filed: March 21, 2006

Docket No.: 127438

For: MAGNETIC TUNNEL JUNCTION DEVICE AND WRITING/READING METHOD FOR
SAID DEVICE

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

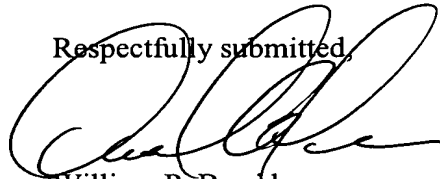
Sir:

Pursuant to 37 CFR §1.56, the attention of the Patent and Trademark Office is hereby directed to the references listed on the attached PTO-1449. Unless otherwise indicated herein, one copy of each reference is attached. It is respectfully requested that the information be expressly considered during the prosecution of this application, and that the references be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

- ☒ 1. This Information Disclosure Statement is being filed (a) within three months of the U.S. filing date of this non-CPA application, OR (b) before the mailing date of a first Office Action on the merits in the present application. No certification or fee is required.
- ☒ 2. Relevance of one or more non-English language reference is discussed in the present specification. See References 11 & 12.
- ☒ 3. One or more reference cited herein was cited in the International Search Report. An English language version of the International Search Report is attached for the Examiner's information. See References 6-17 and 20-22.
- ☒ 4. In accordance with 37 CFR §1.98(a)(2)(ii), copies of any U.S. patents and patent application publications are not attached.
- ☒ 5. An English language Abstract of one or more non-English language reference is attached hereto. See References 14, 18 and 19.

- ☒ 6. A computer-generated English language translation of one or more Japanese Patent Publication cited herein has been obtained from the website of the Japanese Patent Office ([http://www.jpo.go.jp]), and is attached, but has not been reviewed for accuracy. See Reference 14.
- ☒ 7. Reference 1 corresponds to reference 9. Reference 2 corresponds to reference 13. Reference 3 corresponds to reference 12. References 4 and 18 correspond to reference 11. Reference 5 corresponds to reference 17. Reference 19 corresponds to reference 15.

Respectfully submitted,



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WPB:DAT/crh

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DEPOSIT ACCOUNT USE AUTHORIZATION Please grant any extension necessary for entry; Charge any fee due to our Deposit Account No. 15-0461
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IAP9 Rec'd PCT/PTO 21 MAR 2006

Form PTO-1449 (REV. 1/06)		US Dept. of Commerce PATENT & TRADEMARK OFFICE		ATTY DOCKET NO. 127438		APPLICATION NO. New U.S. National Stage of PCT/FR2004/002517	
INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)				APPLICANTS Bernard DIENY et al. FILING DATE March 21, 2006			
U.S. PATENT DOCUMENTS							
Examiner Initials	Cite No.	Document Number	Date	Name			
	1	2002/0089874 A1	07/11/2002	NICKEL et al.			
	2	2003/0206434 A1	11/06/2003	LEUSCHNER			
	3	6,535,416	03/18/2003	DAUGHTON et al.			
	4	2005/0002228 A1	01/06/2005	DIENY et al.			
	5	2005/0002267 A1	01/06/2005	DAUGHTON et al.			
	6	2004/00095801 A1	05/20/2004	STIPE			
	7	6,385,082 B1	05/07/2002	ABRAHAM et al.			
	8	2003/0007398 A1	01/09/2003	DAUGHTON et al.			
	9	2003/0123282 A1	07/03/2003	NICKEL et al.			
	10	5,933,365	08/03/1999	KLERSY et al.			
FOREIGN PATENT DOCUMENTS							
Examiner Initials	Cite No.	Document Number	Date	Country	With English Abstract	With English Translation	
	11	FR 2 832 542	05/23/2003	FRANCE			
	12	WO 00/79540 A1	12/28/2000	WIPO			
	13	WO 03/094170 A2	11/13/2003	WIPO			
	14	JP A 11-175921	07/02/1999	JAPAN	X	X	
	15	FR 2 829 867	03/21/2003	FRANCE			
	16	WO 03/077257 A1	09/18/2003	WIPO			
	17	WO 2005/001490 A2	01/06/2005	WIPO			
	18	WO 03/043017 A1	05/22/2003	WIPO	X		
	19	WO 03/025946 A1	03/27/2003	WIPO	X		
OTHER DOCUMENTS							
Examiner Initials	Cite No.	(Including Author, Title, Date, Pertinent Pages, etc.)					
	20	BOULOUZ et al; "Preparation and characterization of MOCVD bismuth telluride thin films"; Journal of Crystal Growth; Vol. 194, 1998, XP000669099; pp. 336-341					
	21	ZOU et al; "Growth of p- and n-type bismuth telluride thin films by co-evaporation"; Journal of Crystal Growth; Vol. 222, 2001, XP004228292; pp. 82-87					
	22	SOUSA et al; "Bias current heating in spin dependent tunnel junctions"; September 26, 2003; XP002280171; pp. 1-3					
EXAMINER					DATE CONSIDERED		
Examiner: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							

Date: March 21, 2006